



Engineering Test Report

Design of 5V*2.4A Charger with SC1225K (InnoSwitch)

Features :

- Build in Secondary Sync-Rectification. Efficiency Ratings exceeded DoE & CoC_v5.0;
- Integrated-Secondary Side Regulation with Fast DLR;
- Complete System and Output Protections (SCP, OPP, OCP, OVP, OTP).
- Simple Transformer Design



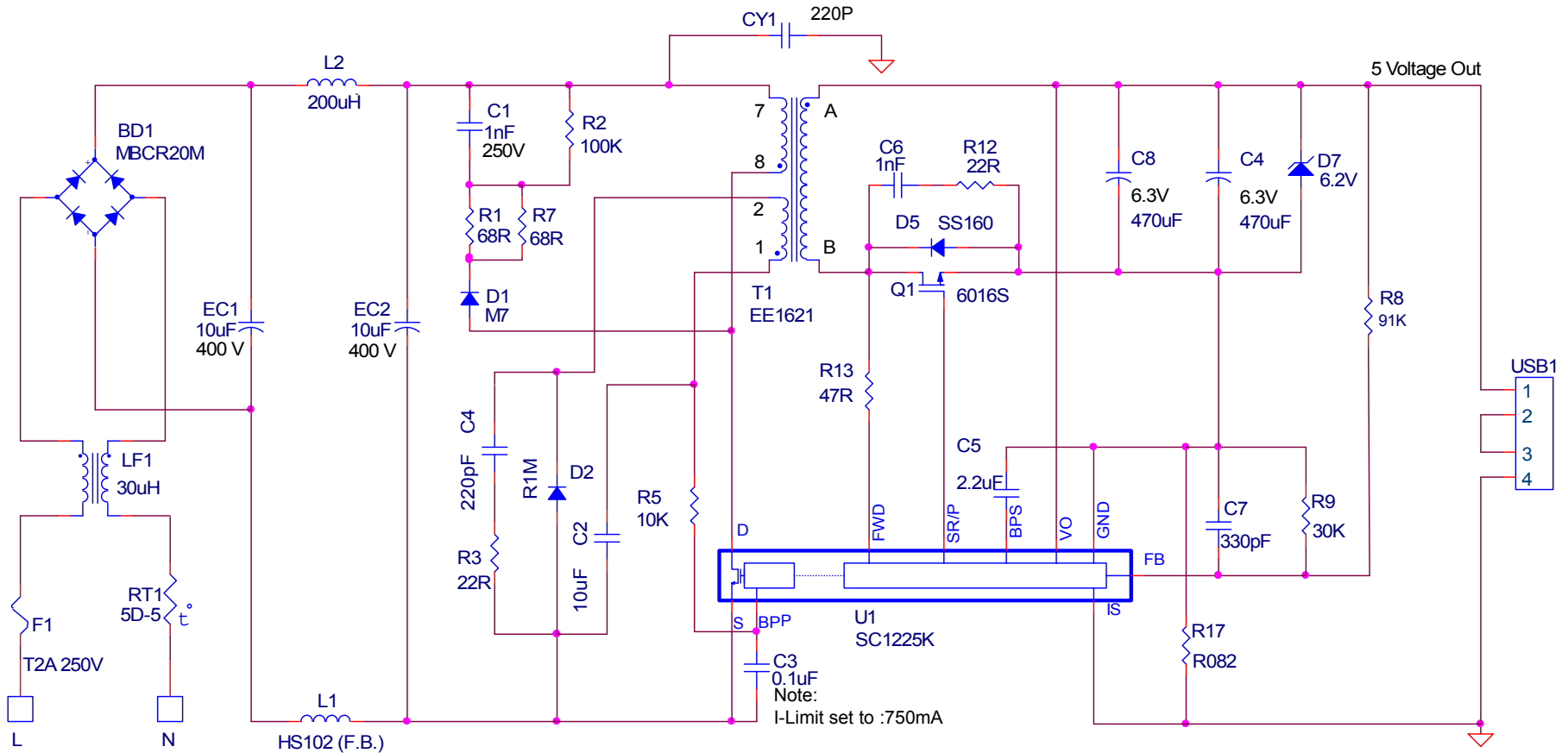
2-Sep-2014, Rev-1
RL (PI-Shenzhen)

Demo Design # PI-C-USB-50 (Rev-1)

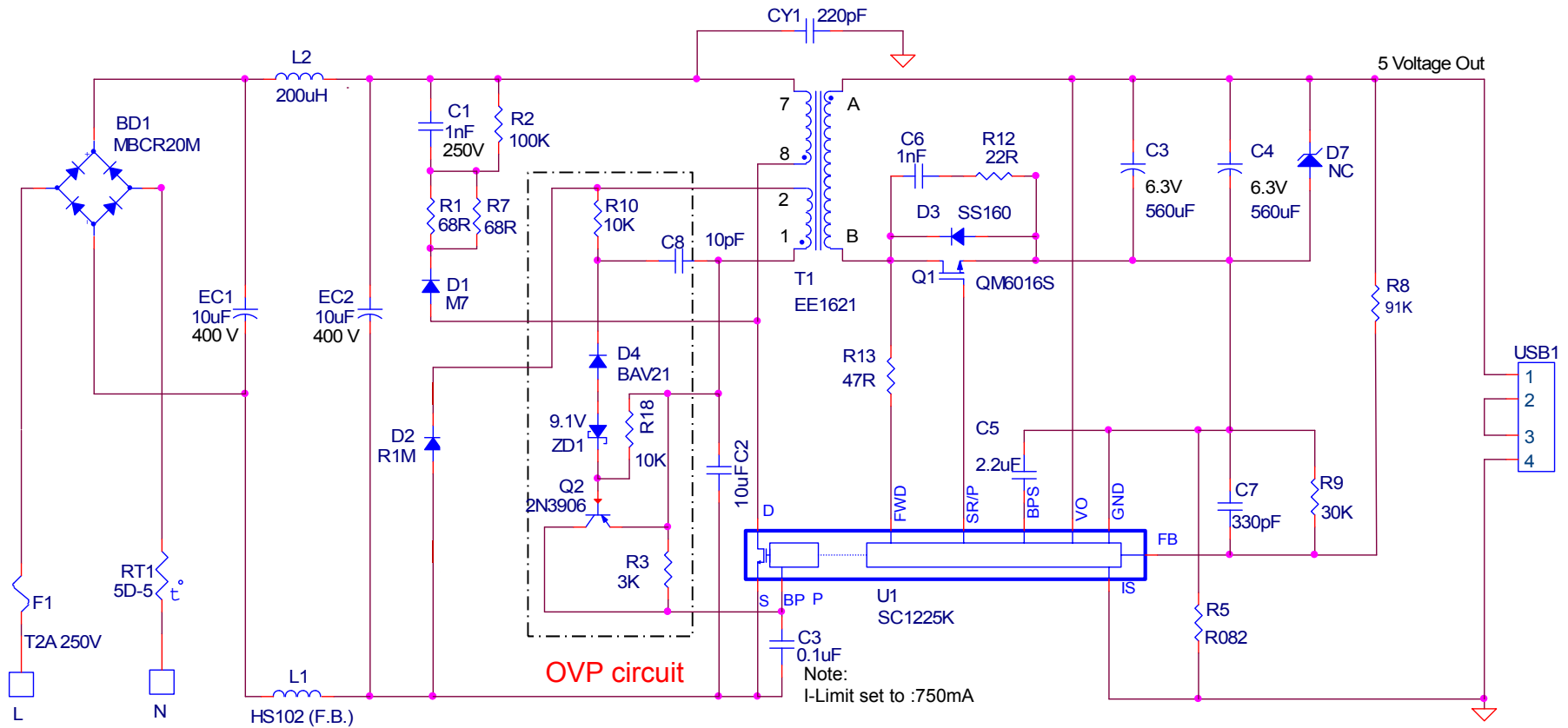
1. Power Supply Specification

Description	Symbol	Min	Typ	Max	Units	Comment/Conditions
INPUT						
Voltage	V_{IN}	90		264	V_{AC}	2 Wire no P.E
Frequency	f_{LINE}	47	50/60	63	Hz	
No-load Input Power	P_{IN}			30	mW	Input 230 V_{AC}
OUTPUT						
Output Voltage	V_{OUT}	4.85	5.00	5.25	V	Measured at the End of Cable,
Output Current	I_{OUT}	2.4			A	
Output Ripple Voltage	V_{RIPPLE}			150	mV _{p-p}	Measured at the End of PCB
Total Output Power						
Continuous Output Power	P_{OUT}	12			W	
Peak Output Power	P_{OUT_PK}				W	
Conducted EMI Margin		6			dB	CISPR22B/EN55022 class B
Average Efficiency	h				%	115 and 230 V_{AC}
Ambient Temperature	T_{AMB}			40	°C	Free convection, sea level
Surge Test			TBD		kV	
Safety		Designed to meet IEC950, UL1950 Class II				

2. Schematic – General



3. Schematic – Added Primary OVP



4. BOM

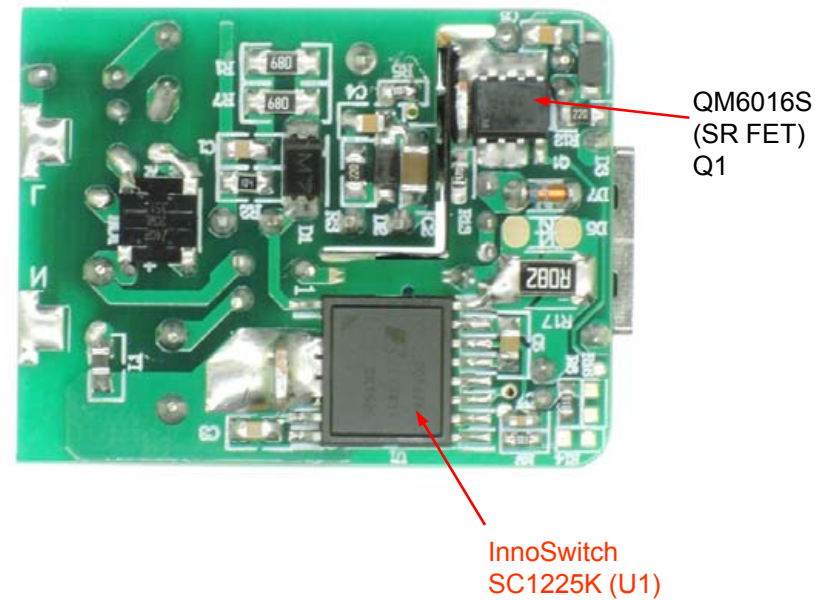
Number	Quantity	Reference	Value	Description
1	2	EC1,EC2	10uF	10uF, 400 V, Electrolytic, 10 x 10
2	2	C3,C4	560uF	560uF,6.3V, Solid cap ,(8 x 9)
3	1	C1	1nF	1nF, 250V, Ceramic, X7R,0805
4	1	C2	10uF	10uF, 50V, Ceramic, X7R, 1206, part number :GJ831CR61E106KE83
5	1	C4	220pF	220pF, 100V, Ceramic, X7R,0805
6	1	C6	1nF	1nF, 100V, Ceramic, X7R,0805
7	1	C3	0.1uF	100 nF, 50 V, Ceramic, 0805
8	1	C5	2.2uF	2.2uF, 25 V, Ceramic, X7R, 0805
9	1	C7	330pF	330pF, 25 V, Ceramic, X7R, 0603
10	1	C8	10pF	10pF, 100V, Ceramic,X7R,0603
11	1	Q1	QM6016S	60V,6A, N-Channel Mosfet, SO-8
12	1	Q2	2N3906	2N3906,PNP transistor.
13	1	CY1	220pF	100pF, 250VAC, Y1
14	1	BD1	MBCR20M	1000V, 2 A, Rectifier
15	1	D1	M7	1000V, 1 A, Rectifier SMA
16	1	D2	RIM	1000V, 0.8 A, Fast Rectifier, Sub SMA
17	1	D4	BAV21	250V,small signal diode, SOD123
18	1	D5	SS160	60 V, 1A, Schottky, Sub SMA
19	1	ZD1	9.1V	15V, Zenner, DL-35
20	1	F1	2A	2A, 250V, Time-lag fuse,
21	1	RT1	5R	5D-5, 5R, 2A, Thermistor
22	1	LF1	30uH	30uH, NiZn toroild CM Choke
23	1	L2	200uH	200uH,Drum inductor ,5X7
24	1	L1	1K	Bead , 1K @ 100Mhz
25	2	R1,R7	68 R	68R, 5%,Thick Film, 1206
26	1	R2	100 K	100 K,5%,Thick Film, 0805
27	1	R3	3K	3K, 5%,Thick Film, 0603
28	2	R4	22 R	22 R, 5%,Thick Film, 0603
29	1	R10	10K	10K, 5%,Thick Film, 0603
30	1	R12	22R	22 R, 5%,Thick Film, 0805
31	1	R13	47R	47R, 5%,Thick Film, 0805
32	1	R8	91 K	91 K, 1%,Thick Film, 0603
33	1	R9	30 K	30 K, 1%,Thick Film, 0603
34	1	R17	R082	82m, 1%,Thick Film, 2516
35	1	R18	10K	10K, 5%,Thick Film, 0603
36	1	T1	EE1621	Extended Bobbin, EE1621, wide core, Vertical
37	1	U1	SC1225k	Innoswitch, SC1225K, 100kHz, 4D-FET, A/R=65%, CDC=6%, CC 2A (Current Limit set to 750mA by C3, 100nF)
38	2	HS	HS	Heatsink
Total :	43			

5 Circuit Board

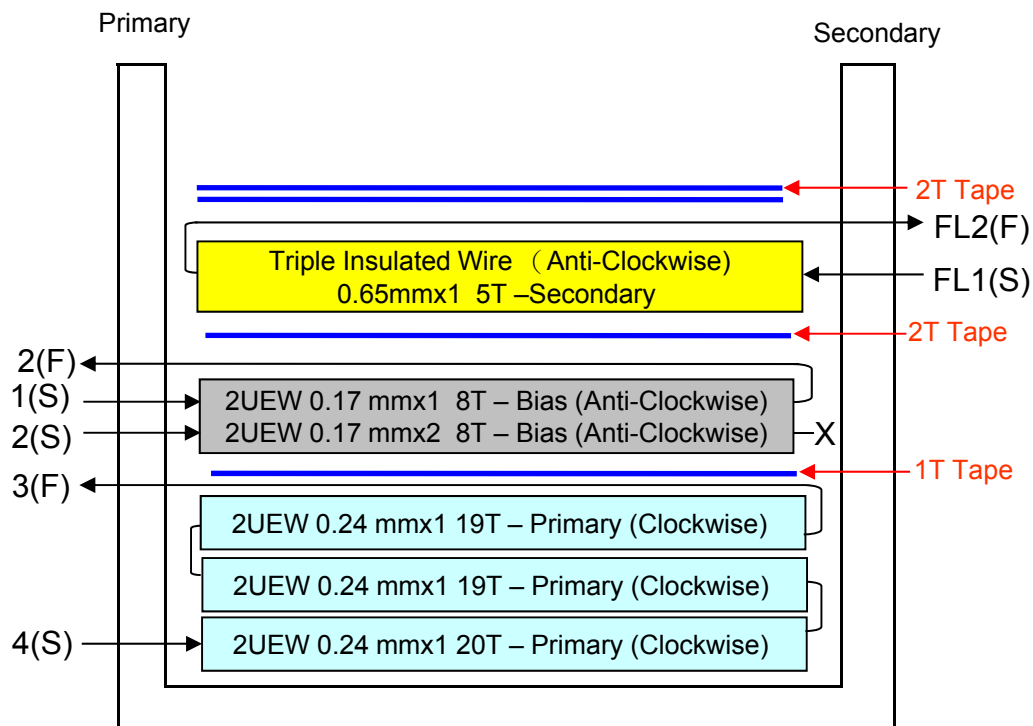
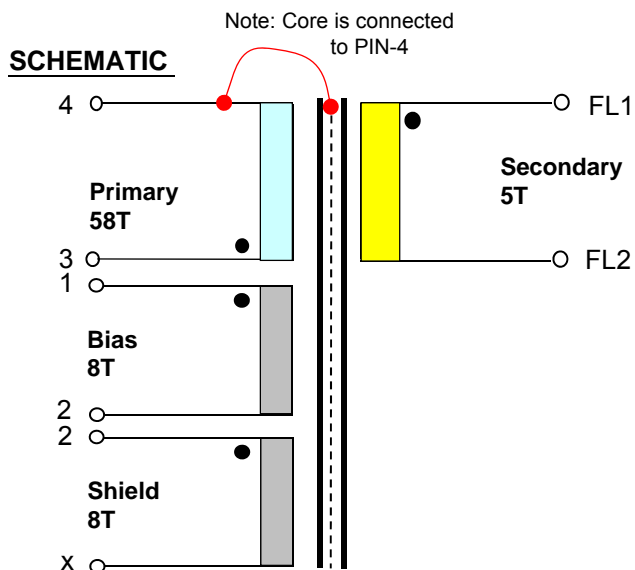
Component side



Solder side



7. Transformer Information



ELECTRICAL SPECIFICATIONS:

1. Primary Inductance (Lp) = 640uH± 7% @100KHz
2. Primary Leakage Inductance 50uH
3. Electrical Strength = 3KV, 50/60Hz, 1Min

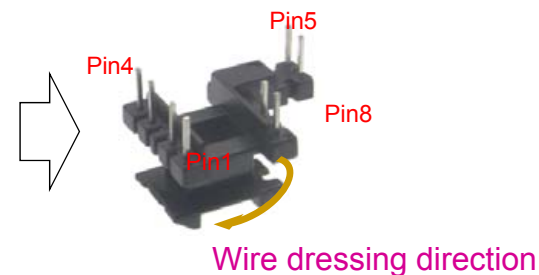
MATERIALS:

1. Core : EE1621 (Ferrite Material TDK PC40 or equivalent, Ae=33mm^2, Bw=5.4mm)
2. Bobbin : ELPD16 (4pin+2pin).
3. Magnet Wires (Pri) : Type 2-UEW
4. Magnet Wire (Sec) : Triple Insulated Wires

FINISHED :

1. Varnish the complete assembly

Wire started in clockwise direction from pin-3 and ended at pin-4 when looking from the bottom side of the bobbin(right photo)



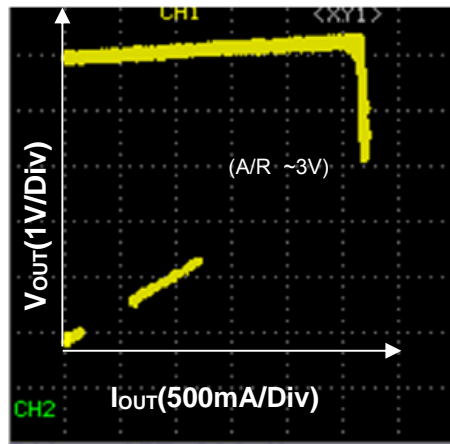
8. Regulation, Ripple & Efficiency Measurement

*** Note: Output voltage & Ripple is measured at PCB End.**

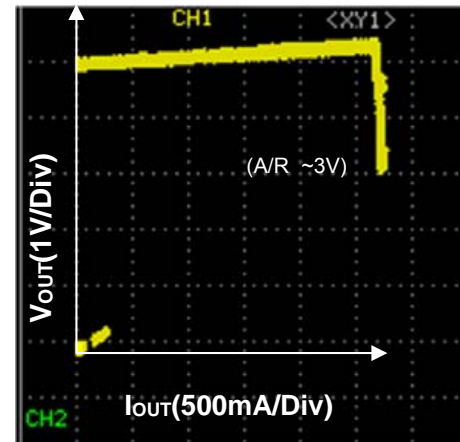
V _{IN} (V _{AC})	P _{IN} (W)	V _{OUT} (V)	I _{OUT} (mA)	V _{RIPPLE} (mV _{P-P})	P _{OUT} (W)	η (%)	Average η(%)	DOE η (%)
90	0.008	5.05	0	30	0	0	84.53	79.94
	3.59	5.13	600	35	3.08	85.67		
	7.40	5.21	1200	65	6.26	84.54		
	11.30	5.28	1800	60	9.51	84.17		
	15.34	5.35	2400	55	12.84	83.73		
115	0.080	5.05	0	30	0	0	84.86	
	3.64	5.13	600	35	3.08	84.52		
	7.34	5.21	1200	65	6.25	85.18		
	11.18	5.28	1800	65	9.50	85.01		
	15.15	5.35	2400	55	12.84	84.75		
230	0.010	5.05	0	35	0	0	84.26	
	3.75	5.13	600	40	3.08	82.08		
	7.42	5.21	1200	50	6.25	84.32		
	11.15	5.28	1800	75	9.50	85.24		
	15.06	5.36	2400	70	12.86	85.42		
264	0.012	5.05	0	35	0	0	83.88	
	3.77	5.13	600	40	3.08	81.64		
	7.49	5.21	1200	50	6.25	83.47		
	11.19	5.29	1800	75	9.52	85.09		
	15.08	5.36	2400	70	12.86	85.31		

9. Output VI Characteristic

(Measured at PCB end)

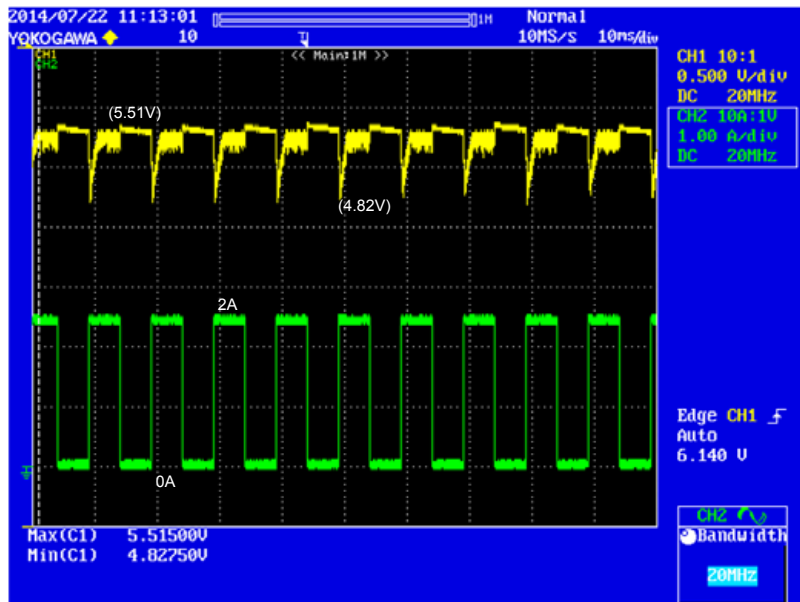


$V_{IN}=90Vac$



$V_{IN}=264Vac$

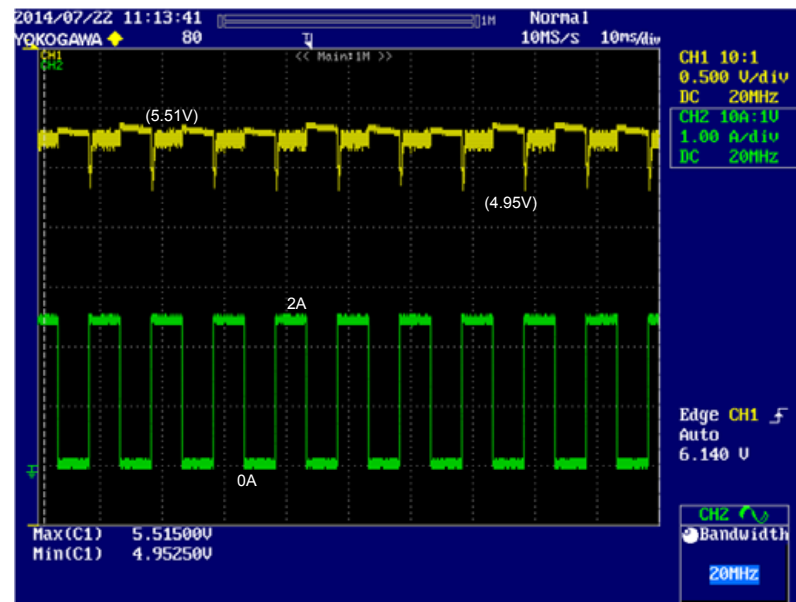
10. DLR Load Response (5ms/5ms,measure at PCB end)



CH4: Output Voltage, 0.5V/Div
CH2: Output Current, 1A/Div

Test Conditions:

1. AC input = 90VAC
2. Load range: 0A-2.4A-0A
3. Frequency: 100Hz(5ms/5ms)
4. Slew rate: 0.25A/S

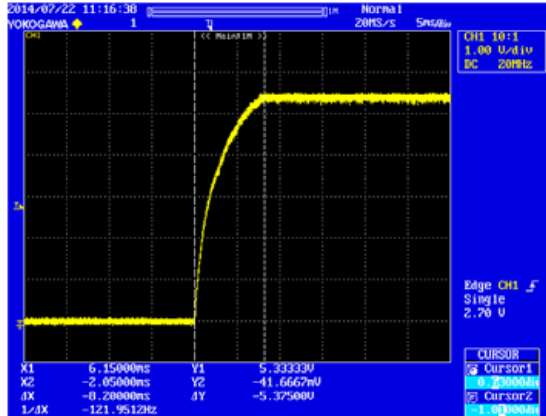


CH1: Output Voltage, 0.5V/Div
CH2: Output Current, 1A/Div

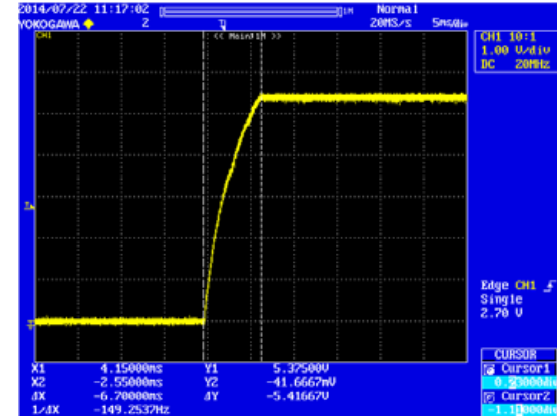
Test Conditions:

1. AC input = 264VAC
2. Load range: 0A-2.4A-0A
3. Frequency: 100Hz(5ms/5ms)
4. Slew rate: 0.25A/S

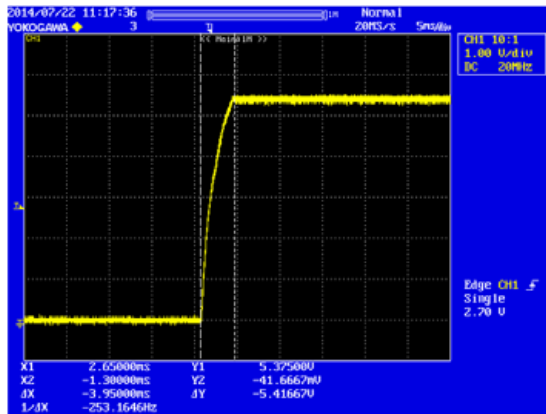
11. Output Rise Time (2A load)



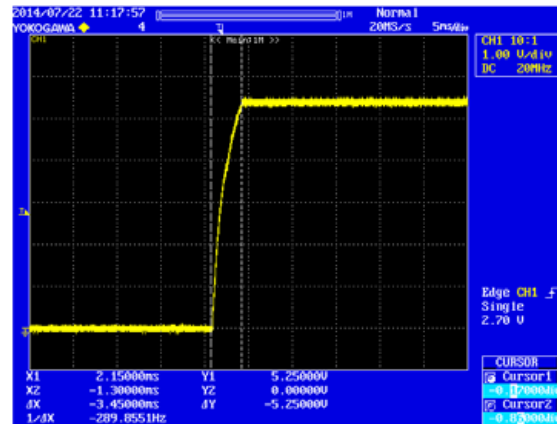
90Vac
Rise time=8.2ms



115Vac
Rise time=6.7ms

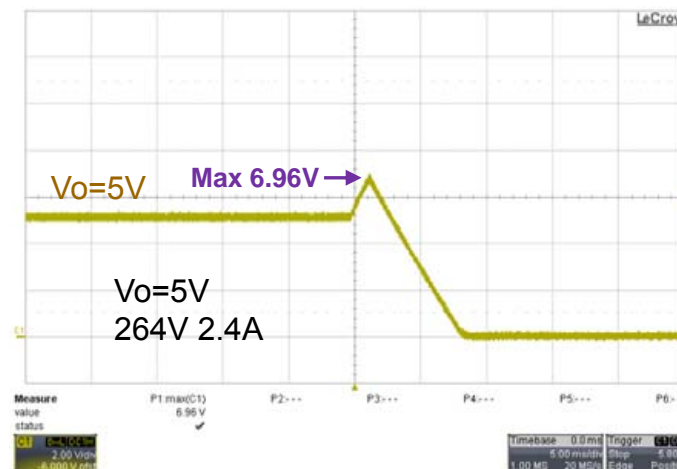
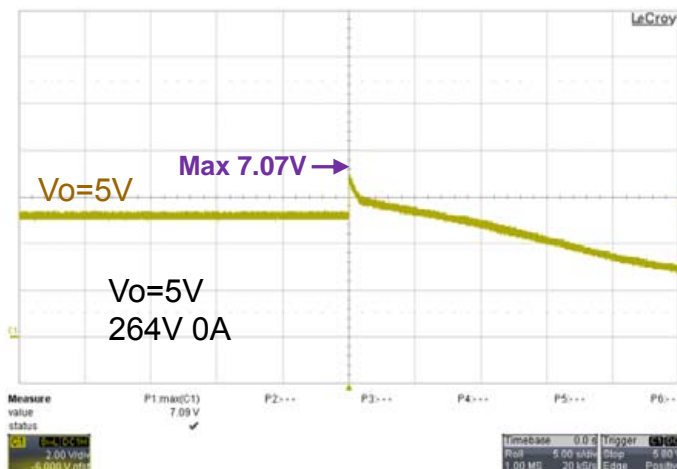
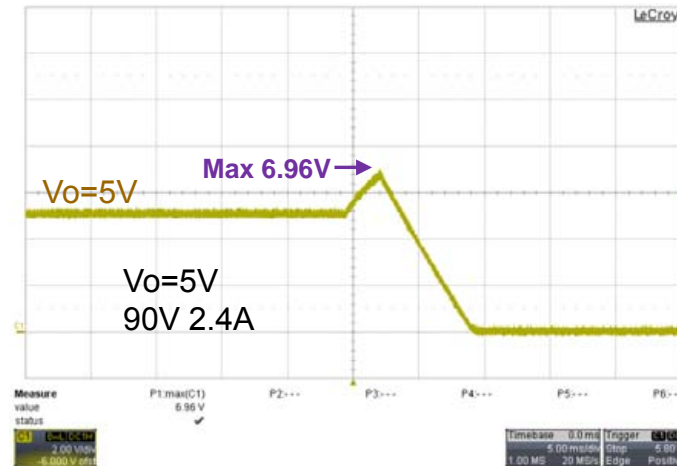
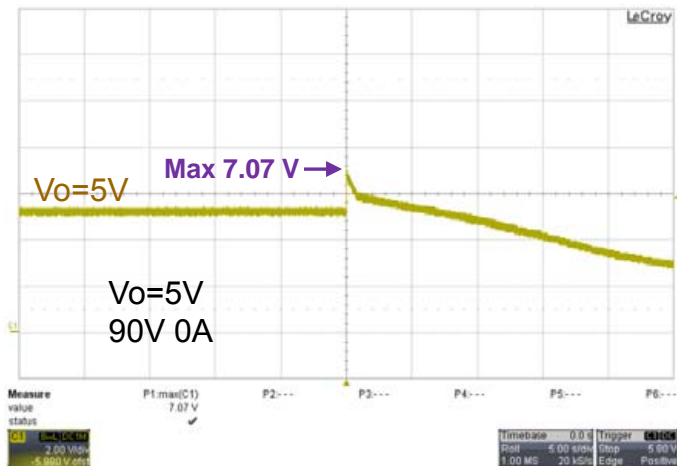


230Vac
Rise time=3.9ms

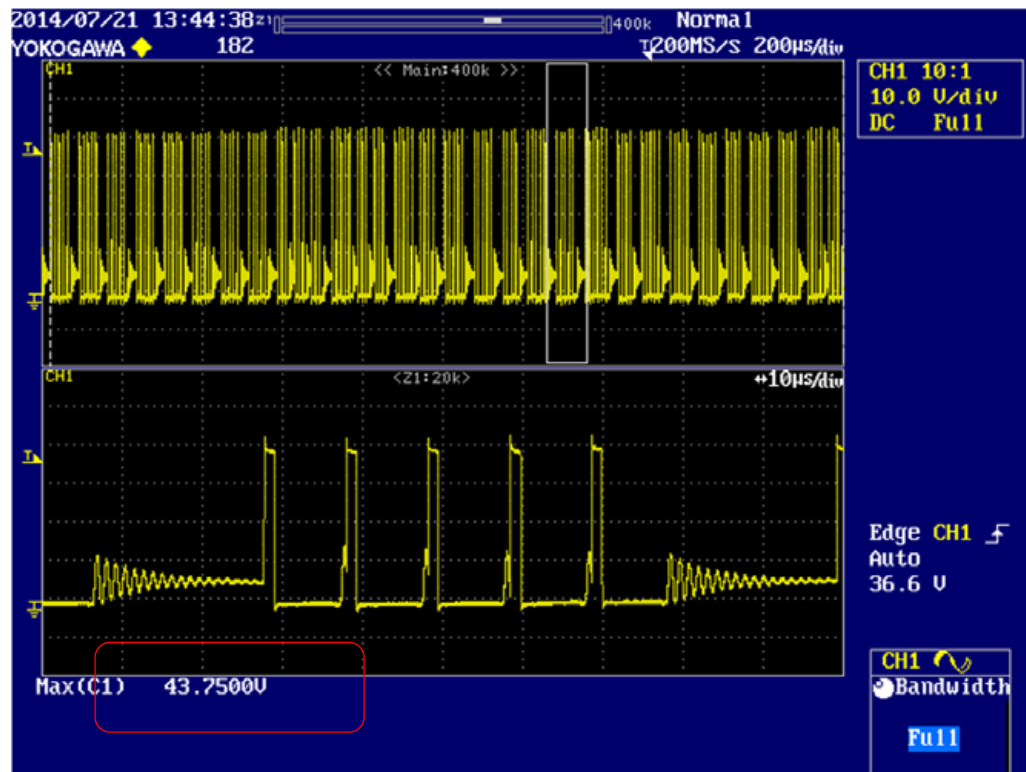


264Vac
Rise time=3.45ms

12. OVP Test (with Primary OVP)



13. Output SR-FET Maximum PIV



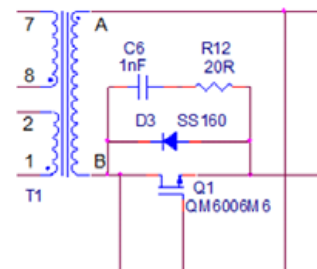
Test Condition:

$V_{IN}=264V_{AC}$, $I_{out}=2.4A$

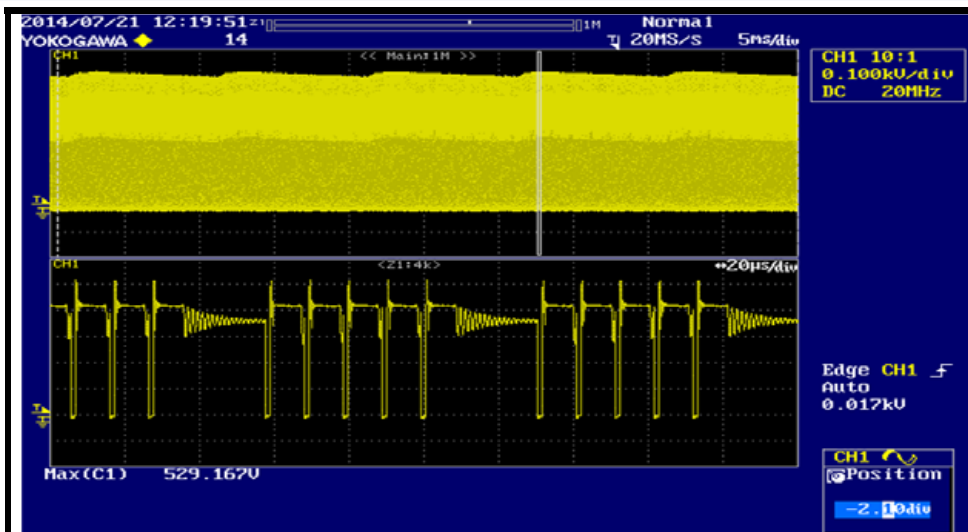
RESULT: PIV= 43.7V

Device used :

- a) SR-FET (Q1) = *QM6016S@6A/60V;
- b) Parallel Diode (D3) : SS160 @1A/60V



14. Maximum Drain Voltage During Start up



Test Condition:

$V_{IN}=264V_{AC}$, $I_{OUT}=2.4A$

Power ON

RESULT: $V_{DRAIN-MAX} = 529V$

(InnoSwitch, SC1225K)

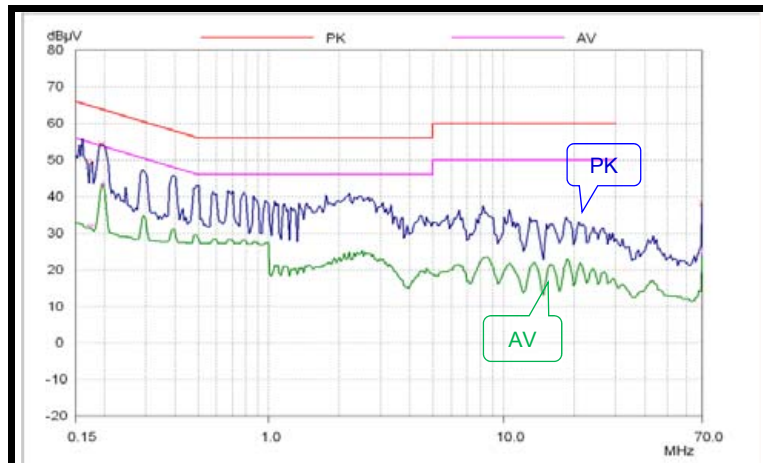
SC1225K

Absolute Maximum Ratings^{1,2}

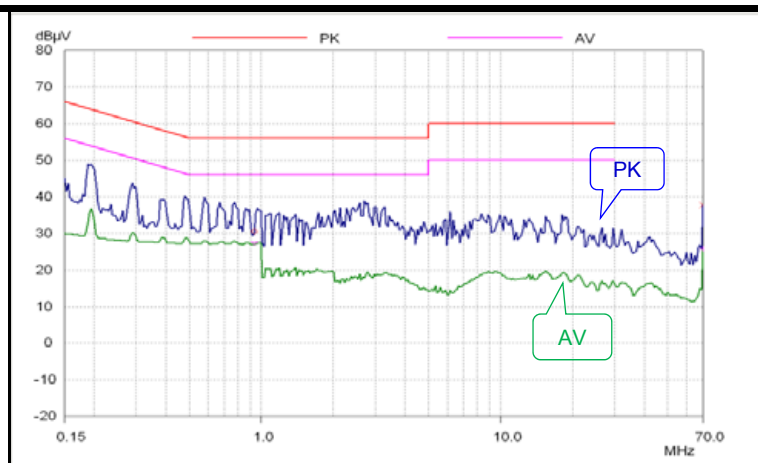
DRAIN Pin Voltage	-0.3 V to 650 V	Lead Temperature	260 °C
DRAIN Pin Peak Current	1360 (2550) mA ³	Notes:	
PRIMARY BYPASS/SECONDARY BYPASS Pin Voltage	-0.3 V to 9 V	1. All voltages referenced to Source and Secondary Ground,	
PRIMARY BYPASS/SECONDARY BYPASS Pin Current	100 mA	$T_c = 25\text{ }^\circ\text{C}$.	
FORWARD Pin Voltage.....	-1.5 V to 70 V	2. Maximum ratings specified may be applied one at a time without causing permanent damage to the product.	
FEEDBACK Pin Voltage	-0.3 to 9 V	Exposure to Absolute Maximum Ratings conditions for extended periods of time may affect product reliability.	
SR/P Pin Voltage	-0.3 to 9 V	3. Higher peak Drain current is allowed while the Drain voltage is simultaneously less than 400 V.	
OUTPUT VOLTAGE Pin Voltage.....	-0.3 to 9 V	4. Normally limited by internal circuitry.	
Storage Temperature	-65 to 125 °C	5. 1/16" from case for 5 seconds.	
Operating Junction Temperature ⁴	-40 to 125 °C		
Ambient Temperature.....	-40 to 85 °C		

15. Conduction EMI (PK and AV)

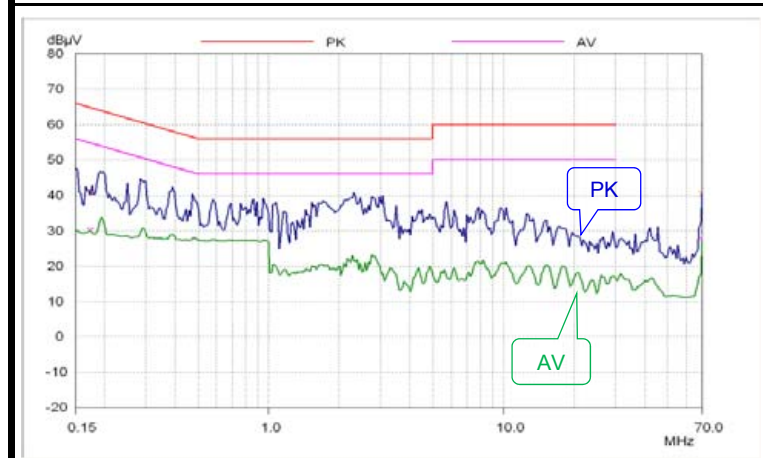
(Output Floating, EN55022 Class-B Limited)



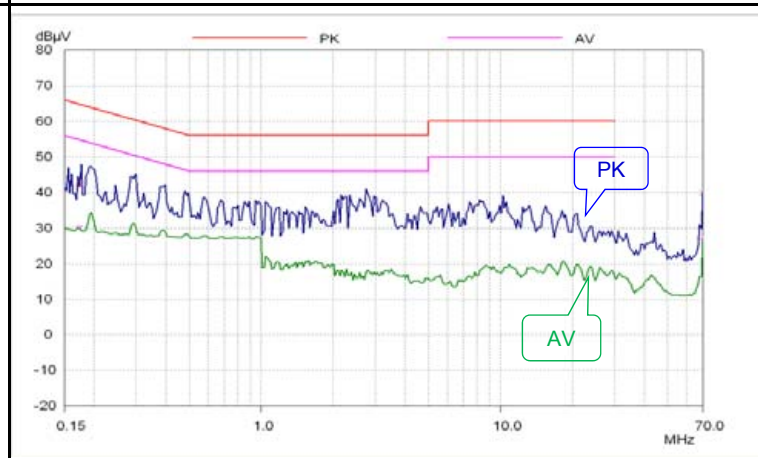
115VAC, L



115VAC, N



230VAC, L



230VAC, N

16.1 RE test



230Vac

16.2 RE test



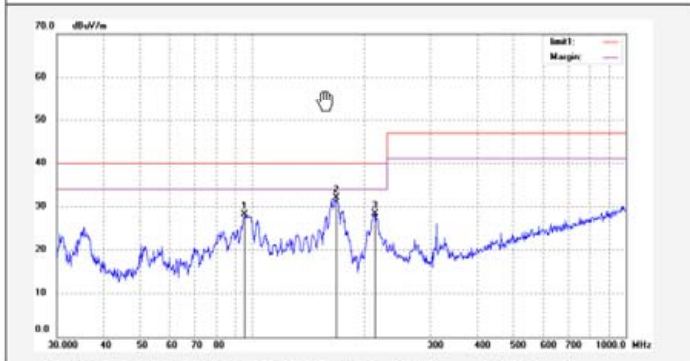
ACCURATE TECHNOLOGY CO., LTD.
F1,Bldg.A,Changyuan New Material Port Keyuan Rd,
Science & Industry Park,Nanshan Shenzhen,P.R.China

Site: 2# Chamber
Tel:+86-0755-26503290
Fax:+86-0755-26503396

Job No.: PI #1801
Standard: EN55022 ClassB Radiated
Test item: Radiation Test
Temp.(C)/Hum.(%) 23 C / 48 %
EUT:
Mode: FULL LOAD
Model: 5V 2.4A
Manufacturer:

Polarization: Horizontal
Power Source: AC 120V/60Hz
Date: 2014/08/26
Time: 16:36:59
Engineer Signature:
Distance: 3m

Note:



No.	Freq. (MHz)	Reading (dBuV/m)	Factor (dB)	Result (dBuV/m)	Limit (dBuV/m)	Margin (dB)	Detector	Height (cm)	Degree (deg.)	Remark
1	95.3131	42.96	-14.72	28.24	40.00	-11.76	peak			
2	167.8136	46.16	-14.03	32.13	40.00	-7.87	peak			
3	213.1035	40.47	-11.99	28.48	40.00	-11.52	peak			



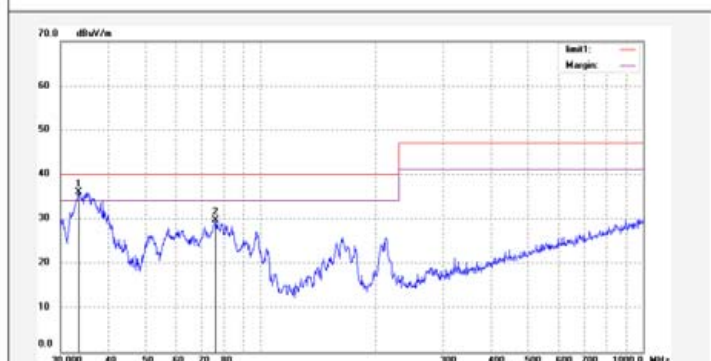
ACCURATE TECHNOLOGY CO., LTD.
F1,Bldg.A,Changyuan New Material Port Keyuan Rd,
Science & Industry Park,Nanshan Shenzhen,P.R.China

Site: 2# Chamber
Tel:+86-0755-26503290
Fax:+86-0755-26503396

Job No.: PI #1800
Standard: EN55022 ClassB Radiated
Test item: Radiation Test
Temp.(C)/Hum.(%) 23 C / 48 %
EUT:
Mode: FULL LOAD
Model: 5V 2.4A
Manufacturer:

Polarization: Vertical
Power Source: AC 120V/60Hz
Date: 2014/08/26
Time: 16:34:32
Engineer Signature:
Distance: 3m

Note:



No.	Freq. (MHz)	Reading (dBuV/m)	Factor (dB)	Result (dBuV/m)	Limit (dBuV/m)	Margin (dB)	Detector	Height (cm)	Degree (deg.)	Remark
1	33.4522	46.17	-10.26	35.91	40.00	-4.09	peak			
2	76.1190	46.44	-16.71	29.73	40.00	-10.27	peak			

120Vac

17. Temperature Rise

Test Setup :

- a) Perform under a controlled temperature chamber with Ambient 40°C;
- b) PCB is being mounted inside an enclosed simulated plastic housing ;
- c) Thermal coupler (type-K) are attached to respective measuring points;
- d) Temperature is recorded after 2 hours from initial turn on.

	Input:90Vac Load:4A	Input:264Vac Load:4A
Components	Temperature(°C)	Temperature(°C)
T-Ambient	40.5	40.3
U1(SC1225K)	98.2	94.8
Core	100.2	99.2
T1(winding)	102.1	101.3
Q1, SR-MOSFET	101.7	103.2
EC3, Solid-Ecap 560uF 6.3V	98.0	99.5
EC2,bulk cap	89.0	82.6



Test set up with UUT inside a simulated casing

18. Product Selection Table

Part used in
current design

Nickname	QC Standard	QC+2A Legacy	Single Output	QC Premium	QC Plus	Single Output
PN	SC1221K	SC1222K	SC1225K	SC1223K	SC1224K	SC1226K
Die Size (FET)	4	4	4	5	5	5
CC [A] on 5V	1.5	2	2	2	2	2
Power Max [W]	15	15	15	20	20	20
Suggested Transformer	ELPD16-8/ RM6	ELPD16-8/ RM6	ELPD16-8/ EPC17	EDR2010/ RM7/8	EDR2010/ RM7/8	EDR2010/ RM7/8
Current Profile	117	176	Not for QC	117	186	Not for QC
Actual (5V, 9V, 12V)	1.5A/1.5A/1.13A	2.0A/1.5A/1.25A	2A	2.0A/2.0A/1.5A	2.0A/1.65A/1.25A	2A
I-llm Low $C_{BP} = 1.0 \mu F$	650	650	650	850	850	850
I-llm Standard $C_{BP} = 0.1 \mu F$	750	750	750	950	950	950
I-llm High $C_{BP} = 10 \mu F$	850	850	850	1050	1050	1050
Cable Drop (CDC)	6%	6%	6%	6%	6%	6%
Auto-Restart (A/R)	65%	65%	65%	65%	65%	65%
Operating Freq.	100kHz	100kHz	100kHz	100kHz	100kHz	100kHz

(for < 15W, part used in current design)

SC1225K InnoSwitch™ Family



Off-Line CV/CC Flyback Switcher IC with Integrated MOSFET, Sync-Rect and Feedback

Product Highlights

Highly Integrated, Compact Footprint

- Incorporates flyback controller, 725 V MOSFET, secondary-side sensing and synchronous rectification
- Integrated, HIPOT-isolated, feedback link
- Exceptional CV/CC accuracy, independent of transformer design or external components
- Instantaneous transient response $\pm 5\%$ CV with 0-100-0% load step

EcoSmart™- Energy Efficient

- <10 mW No-load @ 230 VAC with optional bias winding
- Easily meets all global energy efficiency regulations
- Low heat dissipation

Advanced Protection / Safety Features

- Primary sensed output OVP with optional bias winding
- Secondary sensed output overshoot clamp
- Secondary sensed output OCP to zero output voltage
- Hysteretic thermal shutdown

Full Safety and Regulatory Compliance

- 100% production HIPOT compliance testing at 6 kV DC/1 sec
- Reinforced insulation
- Isolation voltage = 3,500 VAC
- UL1577 and TUV (EN60950) safety approved
- EN61000-4-8 (100 A/m) and EN61000-4-9 (1000 A/m) compliant

Green Package

- Halogen free and RoHS compliant

Applications

- Chargers and adapters for smart mobile devices
- LED lighting
- High efficiency, low voltage, high current power supplies

Description

The InnoSwitch family of ICs dramatically simplifies the development and manufacturing of low voltage, high current power supplies, particularly those in compact enclosures or with high efficiency requirements. The InnoSwitch architecture is revolutionary in that the devices incorporate both primary and secondary controllers, with sense elements and a safety-rated feedback mechanism into a single IC.

Close component proximity and innovative use of the integrated communication link permit accurate control of a secondary-side synchronous rectification MOSFET and optimization of primary-side switching to maintain high efficiency across the entire load range. Additionally, the minimal DC bias requirements of the link, enables the system to achieve less than 10 mW no-load in challenging applications such as smart-mobile device chargers.

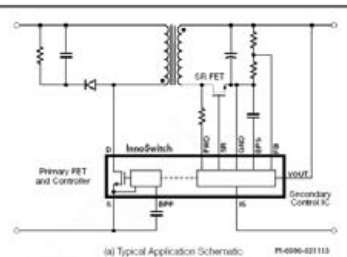


Figure 1. Typical Application Performance

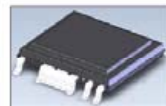


Figure 2. High Creepage, Safety-Compliant eSOP Package.

Output Power Table

Product ¹	230 VAC $\pm 15\%$		85-265 VAC	
	Adapter ¹	Peak or Open Frame ²	Adapter ¹	Peak or Open Frame ²
SC1225K	15 W	20 W	15 W	20 W

Table 1. Output Power Table.

- Notes:
1. Minimum continuous power in a typical non-ventilated enclosed adapter measured at 40 °C ambient. Assumes +12 V output.
 2. Minimum peak power capability.
 3. Package: KR-eSOP-RHS.

www.powerint.com

PRELIMINARY

January 2014

This document contains information on a new product. Specifications and information herein are subject to change without notice.

(for design < 20W)

SC1226K InnoSwitch™ Family



Off-Line CV/CC Flyback Switcher IC with Integrated MOSFET, Sync-Rect and Feedback

Product Highlights

Highly Integrated, Compact Footprint

- Incorporates flyback controller, 850 V MOSFET, secondary-side sensing and synchronous rectification
- Integrated, HIPOT-isolated, feedback link
- Exceptional CV/CC accuracy, independent of transformer design or external components
- Instantaneous transient response $\pm 5\%$ CV with 0-100-0% load step

EcoSmart™- Energy Efficient

- <10 mW No-load @ 230 VAC with optional bias winding
- Easily meets all global energy efficiency regulations
- Low heat dissipation

Advanced Protection / Safety Features

- Primary sensed output OVP with optional bias winding
- Secondary sensed output overshoot clamp
- Secondary sensed output OCP to zero output voltage
- Hysteretic thermal shutdown

Full Safety and Regulatory Compliance

- 100% production HIPOT compliance testing at 6 kV DC/1 sec
- Reinforced insulation
- Isolation voltage = 3,500 VAC
- UL1577 and TUV (EN60950) safety approved
- EN61000-4-8 (100 A/m) and EN61000-4-9 (1000 A/m) compliant

Green Package

- Halogen free and RoHS compliant

Applications

- Chargers and adapters for smart mobile devices
- LED lighting
- High efficiency, low voltage, high current power supplies

Description

The InnoSwitch family of ICs dramatically simplifies the development and manufacturing of low voltage, high current power supplies, particularly those in compact enclosures or with high efficiency requirements. The InnoSwitch architecture is revolutionary in that the devices incorporate both primary and secondary controllers, with sense elements and a safety-rated feedback mechanism into a single IC.

Close component proximity and innovative use of the integrated communication link permit accurate control of a secondary-side synchronous rectification MOSFET and optimization of primary-side switching to maintain high efficiency across the entire load range. Additionally, the minimal DC bias requirements of the link, enables the system to achieve less than 10 mW no-load in challenging applications such as smart-mobile device chargers.

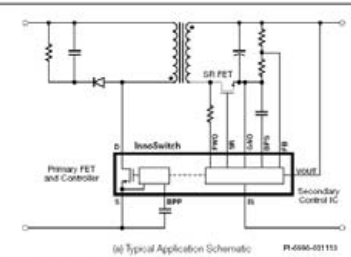


Figure 1. Typical Application Performance

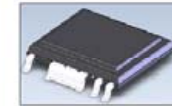


Figure 2. High Creepage, Safety-Compliant eSOP Package.

Output Power Table

Product ¹	230 VAC $\pm 15\%$		85-265 VAC	
	Adapter ¹	Peak or Open Frame ²	Adapter ¹	Peak or Open Frame ²
SC1226K	18 W	22 W	18 W	22 W

Table 1. Output Power Table.

- Notes:
1. Minimum continuous power in a typical non-ventilated enclosed adapter measured at 40 °C ambient. Assumes +12 V output.
 2. Minimum peak power capability.
 3. Package: KR-eSOP-RHS.

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PRELIMINARY

February 2014

This document contains information on a new product. Specifications and information herein are subject to change without notice.

20. SR-FETs (Preferred Sources)



Part used in current design

QM6016S

N-Ch 60V Fast Switching MOSFETs

General Description

The QM6016S is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The QM6016S meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}^1$	8	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}^1$	6.4	A
I_{DM}	Pulsed Drain Current ²	32	A
EAS	Single Pulse Avalanche Energy ³	123	mJ
I_{AS}	Avalanche Current	38	A
$P_{tot} @ T_A = 25^\circ\text{C}$	Total Power Dissipation ⁴	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R_{JA}	Thermal Resistance Junction-Ambient ¹	---	85	$^\circ\text{C}/\text{W}$
R_{JC}	Thermal Resistance Junction-Case ¹	---	24	$^\circ\text{C}/\text{W}$

Rev A.01 D121409

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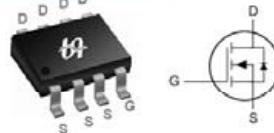
Product Summary

BVDSS	RDSON	ID
60V	12mΩ	8A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- LCD/LED back light

SOP8 Pin Configuration



AO4438
60V N-Channel MOSFET

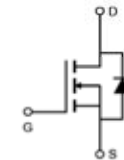
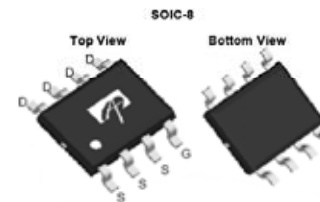
General Description

The AO4438 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.

Product Summary

V_{GS} (V) = 60V
 I_D = 8.2A (V_{GS} = 10V)
 $R_{DS(ON)} < 22\text{m}\Omega$ (V_{GS} = 10V)
 $R_{DS(ON)} < 27\text{m}\Omega$ (V_{GS} = 4.5V)

100% UIS Tested
100% Rg Tested



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^A	I_D	$T_A = 25^\circ\text{C}$	8.2
		$T_A = 70^\circ\text{C}$	6.6
Pulsed Drain Current ^B	I_{DM}		40
Power Dissipation	P_D	$T_A = 25^\circ\text{C}$	3.1
		$T_A = 70^\circ\text{C}$	2
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	R_{JA}	$t \leq 10\text{s}$	24	40
		Steady-State	54	75
Maximum Junction-to-Lead ^C	R_{JL}	21	30	$^\circ\text{C}/\text{W}$

21. Change Revision History

Revision History				
Date	Author	Revision	Description & changes	Reviewed
2 Sep-2014	RL	Rev-1	Initial Release	EH Quek

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